PROCEEDINGS OF SPIE

Oxide-based Materials and Devices V

Ferechteh H. Teherani
David C. Look
David J. Rogers
Editors

2–5 February 2014
San Francisco, California, United States

Sponsored and Published by
SPIE

Volume 8987

Proceedings of SPIE 0277-786X, V. 8987

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Oxide-based Materials and Devices V, edited by Ferechteh H. Teherani, David C. Look,
David J. Rogers, Proc. of SPIE Vol. 8987, 898701 · © 2014 SPIE
CCC code: 0277-786X/14/$18 · doi: 10.1117/12.2063892

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Author(s), "Title of Paper," in *Oxide-based Materials and Devices V*, edited by Ferechteh H. Teherani, David C. Look, David J. Rogers, Proceedings of SPIE Vol. 8987 (SPIE, Bellingham, WA, 2014) Article CID Number.

ISSN: 0277-786X
ISBN: 9780819499004

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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13 Energy Harvesting Storage: Metal Oxides and Graphene
Bruno Viana, Ecole Nationale Supérieure de Chimie de Paris (France)

Introduction

This volume contains the proceedings of the fifth annual "Oxide Based Materials and Devices" conference which was held at SPIE Photonics West in San Francisco. The conference had its most successful year to date in 2014, with 75 oral and 20 poster presentations of excellent quality from groups in 23 countries covering an ever-widening range of both materials and applications. The conference also attracted a growing industrial interest, with presentations from 20 companies ranging in size from start-ups to multinationals.

The chairs wish to thank the SPIE team for their exemplary organization plus all those who contributed and made this a very lively and stimulating conference. We would also especially like to recognize the efforts of those who took the time to contribute a paper and create this valuable and searchable record of the meeting.

We are looking forward to seeing you in San Francisco next February for "Oxide Based Materials and Devices VI"!

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